

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	7.5	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 7.5 A; T _j = 25 °C		-	16	20	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

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5. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain		D	
2	D	drain			
3	G	gate		G (The second s	
4	S	source	3 8 4 Transparent top view	Transparent top view	
5	D	drain			
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255	
7	D	drain			
8	S	source			

6. Ordering information

Table 3. Ordering inf	ormation		
Type number Package			
	Name	Description	Version
PMPB20XNEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMPB20XNEA	3J

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

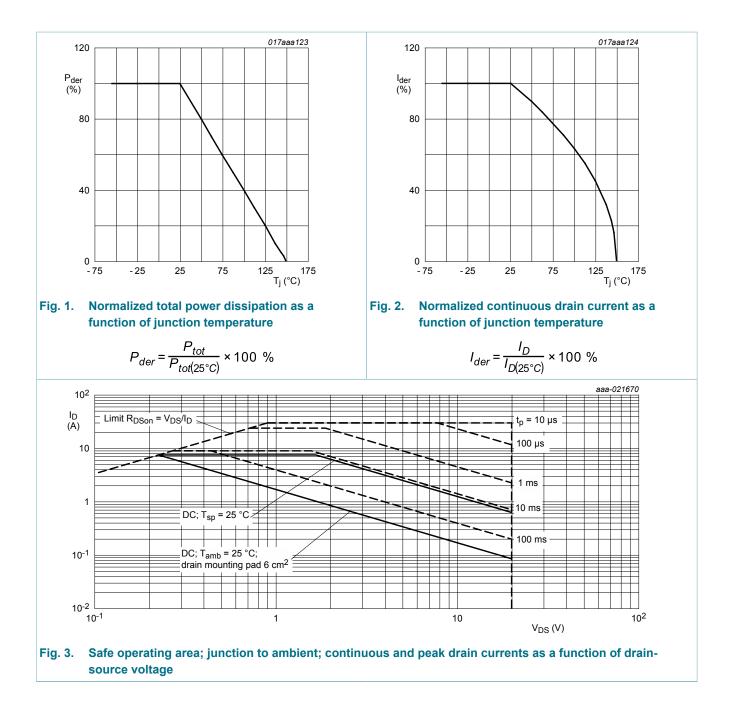
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	7.5	А
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	4.8	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	30	А
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I _D = 1.3 A; DUT in avalanche (unclamped)		-	13	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	460	mW
			[1]	-	1.65	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode		·			-
I _S	source current	T _{amb} = 25 °C	[1]	-	1.65	А
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V
		1				

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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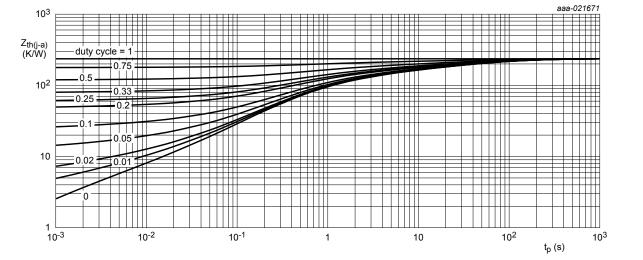


9. Thermal characteristics

Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
fro	thermal resistance		[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

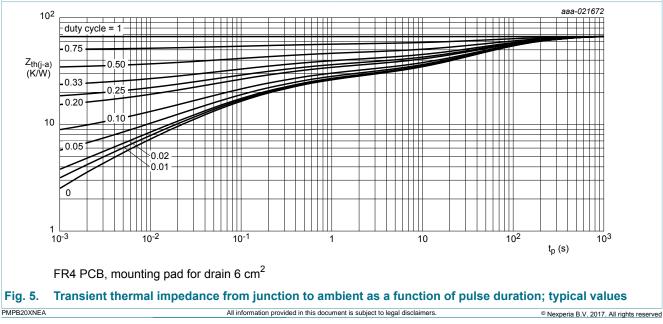
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint





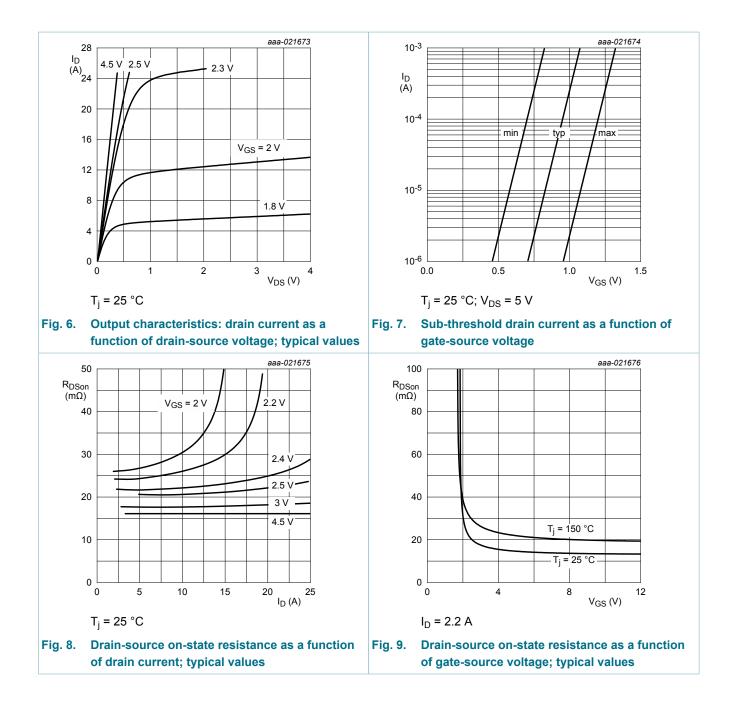
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	0.75	1	1.25	V
I _{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	5	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
		V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 7.5 A; T _j = 25 °C	-	16	20	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 7.5 A; T _j = 150 °C	-	24	30	mΩ
		V _{GS} = 2.5 V; I _D = 6.1 A; T _j = 25 °C	-	24	30	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I _D = 7.5 A; T _j = 25 °C	-	26.8	-	S
R _G	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I _D = 7.5 A; V _{GS} = 4.5 V;	-	9.9	15	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.4	-	nC
Q _{GD}	gate-drain charge	-	-	3.1	-	nC
C _{iss}	input capacitance	V_{DS} = 10 V; f = 1 MHz; V_{GS} = 0 V;	-	930	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	178	-	pF
C _{rss}	reverse transfer capacitance	-	-	144	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I _D = 7.5 A; V _{GS} = 4.5 V;	-	16	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	40	-	ns
t _{d(off)}	turn-off delay time		-	44	-	ns
t _f	fall time	-	-	22	-	ns
Source-dra	ain diode	1		1		
V _{SD}	source-drain voltage	I _S = 1.65 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

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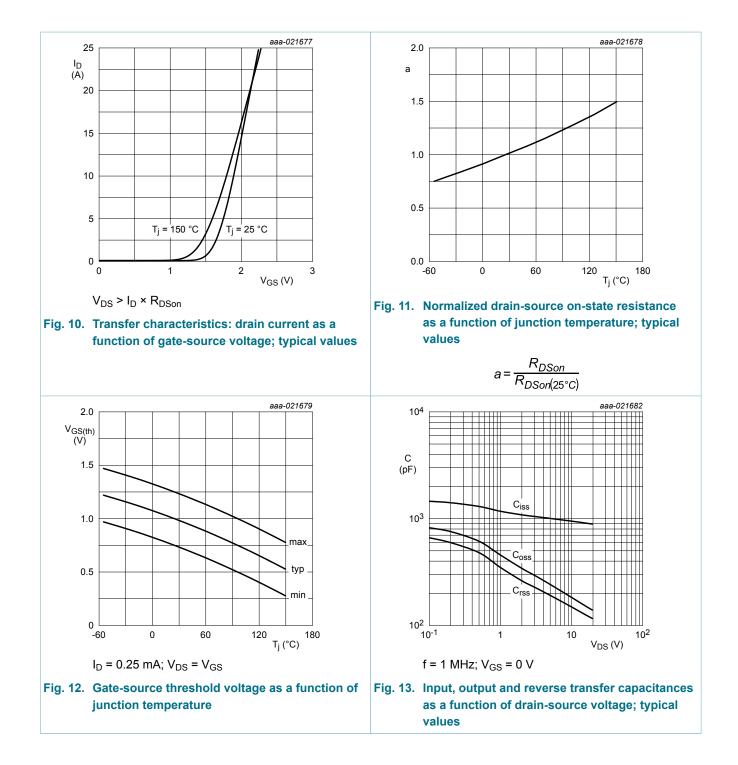
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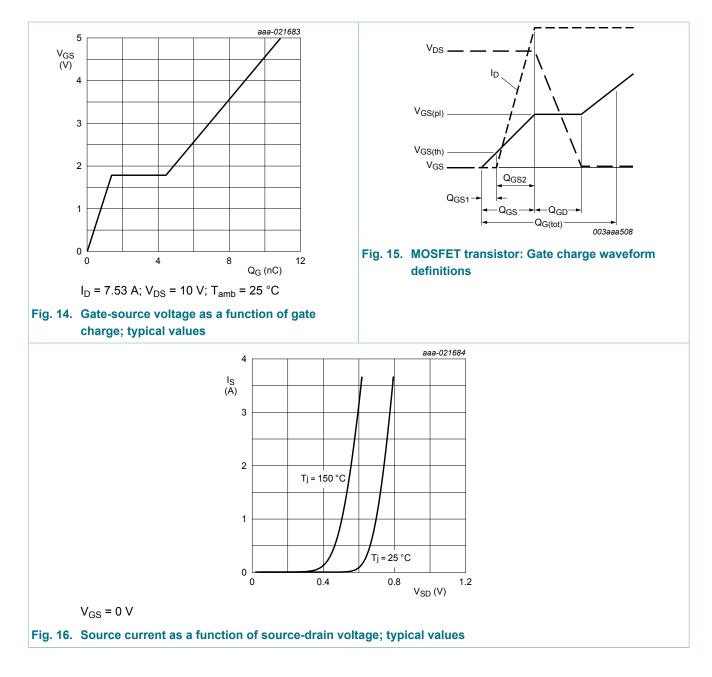
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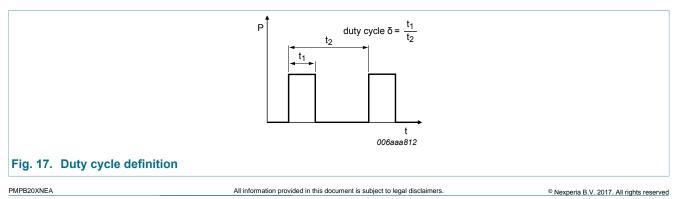
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11. Test information

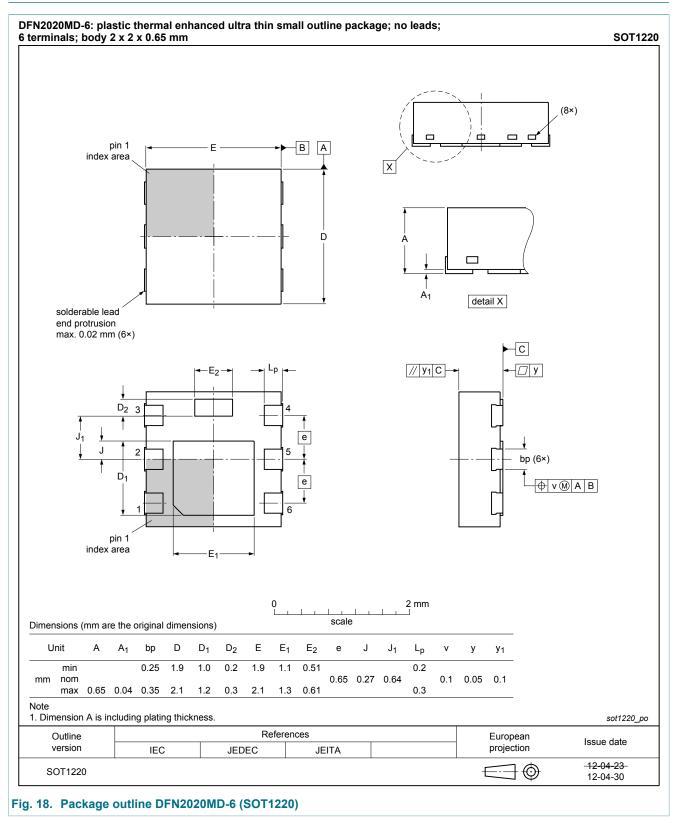


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline

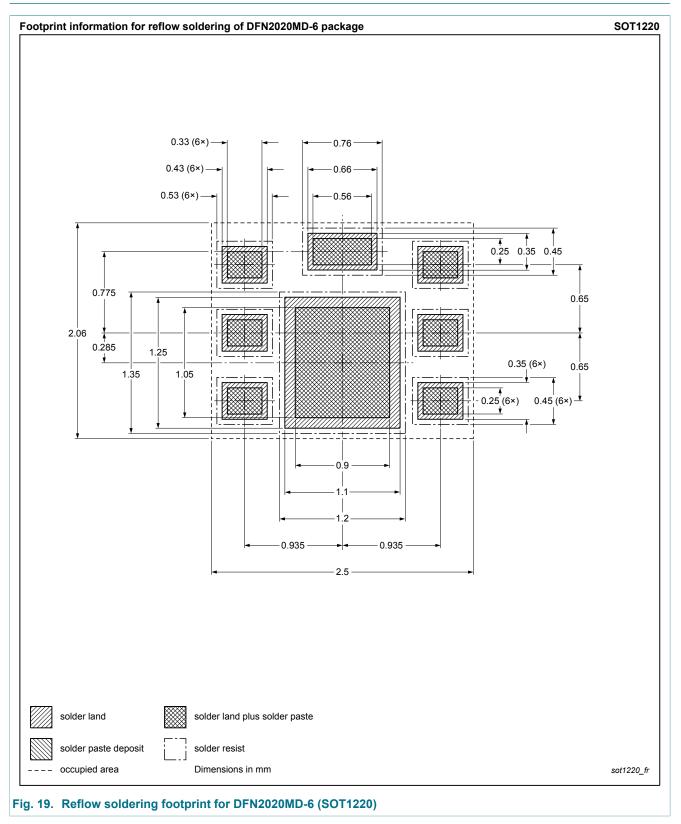


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13. Soldering



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14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB20XNEA v.1	20160222	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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